

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L39	5	(substrate work adj piece workpiece target semiconductor wafer) near10 (block\$3 deflect\$3 shield\$3 shutter\$3 protect\$3) near5 (plasma discharge) and (plasma discharge) near10 (diffus\$4 spread\$4)	USOCR	OR	ON	2005/08/21 11:57
L34	562	29 and (substrate work adj piece workpiece target semiconductor wafer) with (block\$3 deflect\$3 shield\$3 shutter\$3 protect\$3) with (plasma discharge) and (plasma discharge) with (diffus\$4 spread\$4)	US-PGPUB; USPAT	OR	ON	2005/08/21 11:56
L38	40	("0898346" "2378476" "3294669" "3369989" "3604970" "3625848" "3678889" "3691053" "3709809" "3736175" "3783231" "3793179" "4094764" "4197175" "4222838" "4333962" "4361114" "4410407" "4448799" "4466872" "4511593" "4511594" "4556471" "4622452" "4681773" "4724058" "4801839" "4828872" "4856457" "4959242" "5100526").PN. OR ("5656091").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/21 11:48
L37	19	("4511593").URPN.	USPAT	OR	ON	2005/08/21 11:45
L36	9	("2378476" "3625848" "3677924" "3900585" "4094764" "4279216" "4351855").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/21 11:45
L35	413	34 not 30 not 19 not 17 not 15	US-PGPUB; USPAT	OR	ON	2005/08/21 11:40
L33	3225	29 and (substrate work adj piece workpiece target semiconductor wafer) with (block\$3 deflect\$3 shield\$3 shutter\$3 protect\$3) with (plasma discharge)	US-PGPUB; USPAT	OR	ON	2005/08/21 11:40
L31	439	30 not 19 not 17 not 15	US-PGPUB; USPAT	OR	ON	2005/08/21 11:40
L30	549	29 and (substrate work adj piece workpiece target semiconductor wafer) with (block\$3 deflect\$3 shield\$3 shutter\$3 protect\$3) with (ground\$3 earth)	US-PGPUB; USPAT	OR	ON	2005/08/21 11:39

L32	5	("3640812" "3784458" "5178739" "5382339" "6051113").PN. OR ("6444103").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/21 11:35
L18	838	17 not 15	US-PGPUB; USPAT	OR	ON	2005/08/21 11:28
S78	35427	S74 and plasma.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 11:26
L29	76660	L28 and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 11:26
L28	633838	(("118") or ("156") or ("216") or ("438") or ("427") or ("315")).CLAS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/21 11:26
L11	180	(substrate work adj piece workpiece target semiconductor wafer) near10 ((far opposite) near2 (side face)) near10 (electrode anode cathode) and (plasma discharge)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 11:25
L27	34	("3718572" "3956093" "4060470" "4094761").PN. OR ("4324631").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/21 11:03
L26	28	("4361472" "4401546" "4422896" "4434038" "4448653" "4461688" "4601806" "4606802").PN. OR ("4673482").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/21 10:56
L25	22	("3835007" "3941692" "3945903" "4342632" "4597828" "4647361" "4702941").PN. OR ("4964962").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/21 10:53
L24	5	("5417798" "6006694" "6026764" "6170431" "6173674").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/21 10:43
L23	1	("6521081")	USPAT	OR	ON	2005/08/21 10:43
L20	667	19 not 18	US-PGPUB; USPAT	OR	ON	2005/08/21 10:30

L19	729	(substrate work adj piece workpiece target semiconductor wafer) with (shutter shield) with (electrode anode cathode) same (plasma discharge)	US-PGPUB; USPAT	OR	ON	2005/08/21 10:30
L17	883	(substrate work adj piece workpiece target semiconductor wafer) with (outside behind) with (electrode anode cathode) same (plasma discharge)	US-PGPUB; USPAT	OR	ON	2005/08/21 10:29
L1	510	(substrate work adj piece workpiece target semiconductor wafer) near3 (outside) near3 (electrode anode cathode)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 09:58
L16	44	("3762941" "4012307" "4430547" "4705593" "4708766" "4749440" "4857382" "4921157" "5000819" "5045166" "5120568" "5126164" "5147520" "5178682" "5201995" "5225659" "5240559" "5290378" "5292370" "5316739" "5340618" "5368685" "5384167" "5391855" "5399830" "5407121" "5449432" "5499754" "5597438").PN. OR ("5753886").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/21 09:53
L15	398	(substrate work adj piece workpiece target semiconductor wafer) with ((far opposite) near2 (side face)) with (electrode anode cathode) same (plasma discharge)	US-PGPUB; USPAT	OR	ON	2005/08/21 09:48
L13	2230	(substrate work adj piece workpiece target semiconductor wafer) near10 ((far opposite) near2 (side face)) near10 (electrode anode cathode) and (plasma discharge)	US-PGPUB; USPAT	OR	ON	2005/08/21 09:48
L12	178	11 not 8 not 1 not 2 not 4	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 09:41
L9	271	8 not 1 not 2 not 4	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 09:41
L8	367	(substrate work adj piece workpiece target semiconductor wafer) near10 (outside) near10 (electrode anode cathode) and (plasma discharge)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 09:40

L10	1	1987-317249.NRAN.	DERWENT	OR	ON	2005/08/21 09:35
L7	1845	(substrate work adj piece workpiece target semiconductor wafer) and (outside) and (electrode anode cathode) and (plasma discharge)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 09:31
S15 2	13606	(substrate work adj piece workpiece target semiconductor wafer) and (outside) and (electrode anode cathode)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 09:30
S15 5	314	(substrate work adj piece workpiece target semiconductor wafer) near2 (outside) near3 (electrode anode cathode)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 09:22
L6	332	3 5	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 09:22
L5	136	L4 not L1 not L2	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 09:22
L4	459	(substrate work adj piece workpiece target semiconductor wafer) near2 (outside) near5 (electrode anode cathode)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 09:22
L3	196	L1 not L2	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 09:22
L2	314	(substrate work adj piece workpiece target semiconductor wafer) near2 (outside) near3 (electrode anode cathode)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 09:22
S15 6	459	(substrate work adj piece workpiece target semiconductor wafer) near2 (outside) near5 (electrode anode cathode)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 19:53
S15 4	510	(substrate work adj piece workpiece target semiconductor wafer) near3 (outside) near3 (electrode anode cathode)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 19:53
S15 3	708	(substrate work adj piece workpiece target semiconductor wafer) near3 (outside) near5 (electrode anode cathode)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 19:53
S15 1	121016	(substrate work adj piece workpiece target semiconductor wafer) and (outside) and (electrode anode cathode)	US-PGPUB; USPAT	OR	ON	2005/08/19 19:53

S14 7	8470	(substrate work adj piece workpiece target semiconductor wafer) with (outside) with (electrode anode cathode)	US-PGPUB; USPAT	OR	ON	2005/08/19 19:53
S15 0	0	("2005/0061444").URPN.	USPAT	OR	ON	2005/08/19 19:50
S14 9	43	("4597844").URPN.	USPAT	OR	ON	2005/08/19 19:32
S14 8	765	S147 and plasma.ti,ab,clm.	US-PGPUB; USPAT	OR	ON	2005/08/19 19:30
S14 5	13383	(substrate work adj piece workpiece target semiconductor wafer) with (outside) with (electrode anode cathode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 19:29
S14 4	48119	(substrate work adj piece workpiece target semiconductor wafer) with (outside opposite) with (electrode anode cathode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 19:29
S18	104	(156/345.54).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/19 19:27
S14 3	4	("5698328" "5993919").PN. OR ("6200652").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/19 17:38
S14 2	27	("4070264" "4223048" "4289598" "4492716" "4633809" "4633811" "4643952" "4676195" "4735633" "4950376").PN. OR ("5039376").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/19 17:35
S14 1	3	((("5039376") or ("6200652") or ("6852195"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/08/19 17:34
S13 9	3	((("4581118") or ("5891311") or ("6200431"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/08/19 17:34
S14 0	2	JP-62027562-\$..did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 17:16
S13 6	1	("4581118").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/08/18 20:38